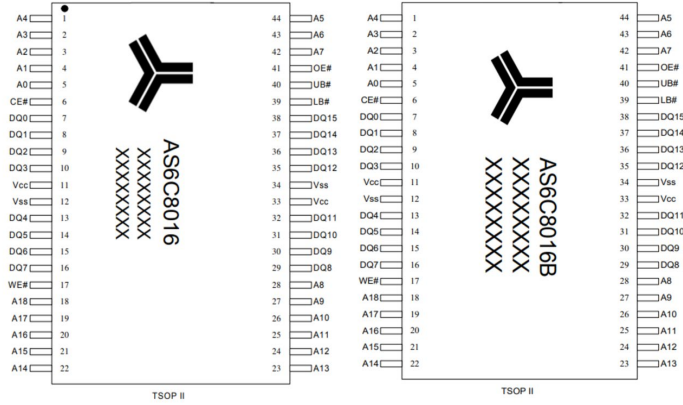


AS6C8016-55ZIN & AS6C8016B-45ZIN Comparison

Part Number & result Parameter	AS6C8016-55ZIN	AS6C8016B-45ZIN	Comments
Product Description	8Mb Wide Voltage Range Low Power ASRAM	8Mb 3V Voltage Low Power ASRAM	
Fab Process Technology	150nm	90nm	Different IPs
Capacity	8Mb	8Mb	Same
Memory Organization	512K x 16bits	512K x 16bits	Same
Operating. Power Supply	V _{CC} = 2.7V ~ 5.5V	V _{CC} = 2.7V ~ 3.6V	Different
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	CIO: 8pf (Max.)	CIO: 8pf (Max.)	Same
Read Cycle Time (t _{RC})	55ns (Min.)	45ns (Min.)	Rev B faster
Write Cycle Time (t _{WC})	55ns (Min.)	45ns (Min.)	Rev B faster
Address Access Time(t _{AA})	55ns (Max.)	45ns (Max.)	Rev B faster
OE Access Time (t _{OE})	30ns (Max.)	25ns (Max.)	Rev B faster
V _{OH} (V) @ -1.0mA	2.4 (Min.)	2.2 (Min.)	Comparable
V _{OL} (V) @ 2mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.4 (Min.)	2.2 (Min.)	Comparable
V _{IL} (V)	0.6 (Max.)	0.6 (Max.)	Same
I _{LI} / I _{LO} (uA)	1 (Max.)	1 (Max.)	Same
Operating Current (55ns)	ICC2 = 60mA (Max. @5.5V)	ICC = 20mA (Max.)	Rev.B better
Operating Current (1us)	ICC1 = 12mA (Max.@5.5V)	ICC1 = 5mA (Max.)	Rev.B better
Standby Current (CMOS)	ISB1 = 50uA (Max.@5.5V)	ISB1 = 20uA (Max.)	Rev.B better
Data Retention Vcc (VDR)	1.5V (Min.)	1.5V (Min.)	Same
Package Type	44pin 400mils TSOP II	44pin 400mils TSOP II	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible			Same